











CSD17581Q3A

SLPS629 - OCTOBER 2016

CSD17581Q3A 30-V N-Channel NexFET™ Power MOSFETs

Features

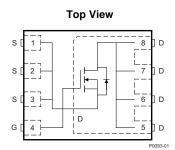
- Low Q_a and Q_{ad}
- Low R_{DS(on)}
- Low Thermal Resistance
- Avalanche Rated
- Lead-Free
- **RoHS Compliant**
- Halogen Free
- SON 3.3-mm x 3.3-mm Plastic Package

Applications

- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom, and Computing Systems
- **Motor Control Applications**
- Optimized for Control FET Applications

Description

This 30-V, 3.2-m Ω , SON 3.3-mm × 3.3-mm NexFET™ power MOSFET is designed to minimize losses in power conversion applications.



R_{DS(on)} vs V_{GS} 10 $T_C = 25^{\circ}C$, $I_D = 16 A$ 9 R_{DS(on)} - On-State Resistance (mΩ) $T_C = 125^{\circ}C$, $I_D = 16$ A 8 6 5 3 2 0 2 12 V_{GS} - Gate-to-Source Voltage (V) D007

Product Summary

$T_A = 25^\circ$	С	TYPICAL VA	UNIT			
V_{DS}	Drain-to-Source Voltage 30					
Q_g	Gate Charge Total (4.5 V)	20	nC			
Q_{gd}	Gate Charge Gate-to-Drain	4	nC			
D	Drain-to-Source On-Resistance	$V_{GS} = 4.5 \text{ V}$ 3.9		mΩ		
R _{DS(on)}	Drain-to-Source On-Resistance	V _{GS} = 10 V 3.2		mΩ		
V _{GS(th)}	Threshold Voltage	1.3	V			

Device Information⁽¹⁾

DEVICE	MEDIA	QTY	PACKAGE	SHIP
CSD17581Q3A	13-Inch Reel	2500	SON	Tape
CSD17581Q3AT	7-Inch Reel	250	3.30-mm × 3.30-mm Plastic Package	and Reel

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Absolute Maximum Ratings

T _A = 2	5°C	VALUE	UNIT	
V_{DS}	Drain-to-Source Voltage	30	٧	
V_{GS}	Gate-to-Source Voltage	±20	V	
	Continuous Drain Current (Package Limited)	60		
I _D	Continuous Drain Current (Silicon Limited), $T_C = 25^{\circ}C$	101	Α	
	Continuous Drain Current ⁽¹⁾	21		
I_{DM}	Pulsed Drain Current ⁽²⁾	154	Α	
D	Power Dissipation ⁽¹⁾	2.8	W	
P_D	Power Dissipation, T _C = 25°C	63	VV	
T _J , T _{stg}	Operating Junction Temperature, Storage Temperature	-55 to 150	°C	
E _{AS}	Avalanche Energy, Single Pulse I _D = 39 A, L = 0.1 mH, R _G = 25 Ω	76	mJ	

(1) Typical $R_{\theta JA} = 45^{\circ}C/W$ on a 1-in², 2-oz Cu pad on a 0.06-in thick FR4 PCB.

> 40 45

(2) Max R_{θ,IC} = 2°C/W, pulse duration ≤100 μs, duty cycle ≤1%.

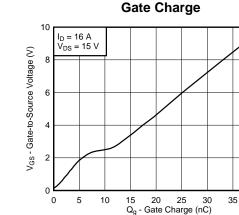






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4 Revision History

DATE	REVISION	NOTES
October 2016	*	Initial release.

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5 Specifications

5.1 Electrical Characteristics

 $T_{\Lambda} = 25^{\circ}C$ (unless otherwise stated)

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
STATIC	CHARACTERISTICS		,		
BV _{DSS}	Drain-to-source voltage	V _{GS} = 0 V, I _D = 250 μA	30		V
I _{DSS}	Drain-to-source leakage current	V _{GS} = 0 V, V _{DS} = 24 V		1	μА
I _{GSS}	Gate-to-source leakage current	V _{DS} = 0 V, V _{GS} = 20 V		100	nA
V _{GS(th)}	Gate-to-source threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0 1.3	1.7	V
Р	Drain-to-source	$V_{GS} = 4.5 \text{ V}, I_D = 16 \text{ A}$	3.9	4.7	O
R _{DS(on)}	On-resistance	$V_{GS} = 10 \text{ V}, I_D = 16 \text{ A}$	3.2	3.8	mΩ
9 _{fs}	Transconductance	V _{DS} = 3 V, I _D = 16 A	78		S
DYNAMI	C CHARACTERISTICS				
C _{iss}	Input capacitance		2800	3640	pF
C _{oss}	Output capacitance	$V_{GS} = 0 \text{ V}, V_{DS} = 15 \text{ V}, f = 1 \text{ MHz}$	342	445	pF
C _{rss}	Reverse transfer capacitance		150	195	pF
R_G	Series gate resistance		1.8	3.6	Ω
Qg	Gate charge total (4.5 V)		20	25	nC
Qg	Gate charge total (10 V)		41	54	nC
Q _{gd}	Gate charge gate-to-drain	V _{DS} = 15 V, I _D = 16 A	4.0		nC
Q _{gs}	Gate charge gate-to-source		6.9		nC
Q _{g(th)}	Gate charge at V _{th}		3.6		nC
Q _{oss}	Output charge	V _{DS} = 15 V, V _{GS} = 0 V	11.7		nC
t _{d(on)}	Turnon delay time		12		ns
t _r	Rise time	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V},$	23		ns
t _{d(off)}	Turnoff delay time	$I_{DS} = 16 \text{ A}, R_G = 0 \Omega$	23		ns
t _f	Fall time		10		ns
DIODE C	CHARACTERISTICS				
V _{SD}	Diode forward voltage	I _{SD} = 16 A, V _{GS} = 0 V	0.8	1.0	V
Q _{rr}	Reverse recovery charge	V _{DS} = 15 V, I _F = 16 A,	10.2		nC
t _{rr}	Reverse recovery time	di/dt = 300 A/μs	9.8		ns

5.2 Thermal Information

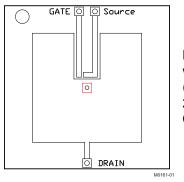
 $T_A = 25$ °C (unless otherwise stated)

	THERMAL METRIC	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-case thermal resistance ⁽¹⁾			2	°C/W
$R_{\theta JA}$	Junction-to-ambient thermal resistance ⁽¹⁾⁽²⁾			55	· C/VV

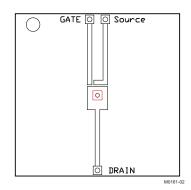
R_{θJC} is determined with the device mounted on a 1-in² (6.45-cm²), 2-oz (0.071-mm) thick Cu pad on a 1.5-in x 1.5-in (3.81-cm x 3.81-cm), 0.06-in (1.52-mm) thick FR4 PCB. R_{θJC} is specified by design, whereas R_{θJA} is determined by the user's board design.

(2) Device mounted on FR4 material with 1-in² (6.45-cm²), 2-oz (0.071-mm) thick Cu.





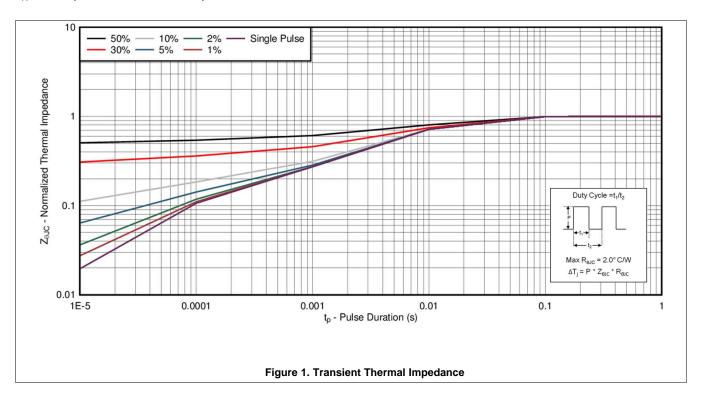
Max $R_{\theta JA} = 55^{\circ} C/W$ when mounted on 1-in² (6.45-cm²) of 2-oz (0.071-mm) thick Cu.



Max $R_{\theta JA} = 160^{\circ} C/W$ when mounted on a minimum pad area of 2-oz (0.071-mm) thick Cu.

5.3 Typical MOSFET Characteristics

 $T_A = 25$ °C (unless otherwise stated)



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10

V_{GS} - Gate-to-Source Voltage (V)

2

0

0

5

10

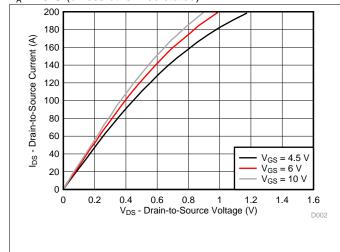
15

 $I_D = 16 A$

20

Typical MOSFET Characteristics (continued)

 $T_A = 25$ °C (unless otherwise stated)



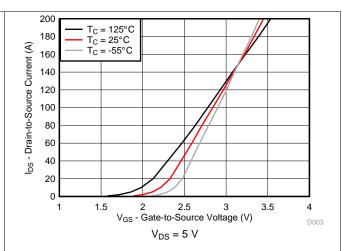


Figure 2. Saturation Characteristics

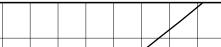


Figure 3. Transfer Characteristics

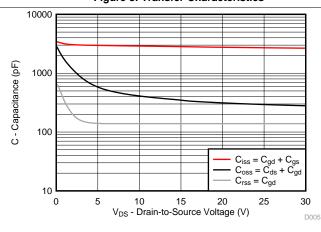


Figure 4. Gate Charge

Q_g - Gate Charge (nC)

25

30

 $V_{DS} = 15 V$

40

45

D004

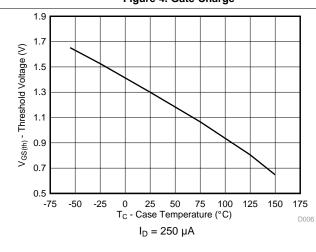


Figure 6. Threshold Voltage vs Temperature

Figure 5. Capacitance

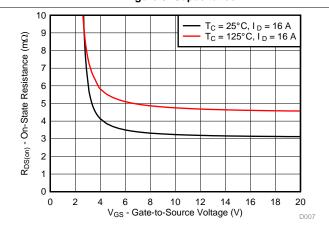
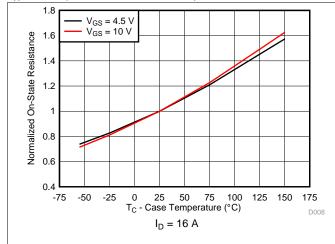


Figure 7. On-State Resistance vs Gate-to-Source Voltage

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Typical MOSFET Characteristics (continued)

 $T_A = 25$ °C (unless otherwise stated)



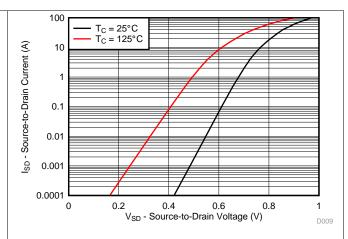
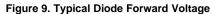
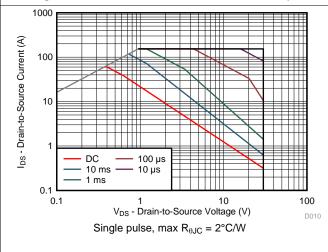


Figure 8. Normalized On-State Resistance vs Temperature





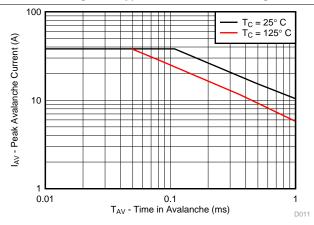


Figure 10. Maximum Safe Operating Area (SOA)

Figure 11. Single Pulse Unclamped Inductive Switching

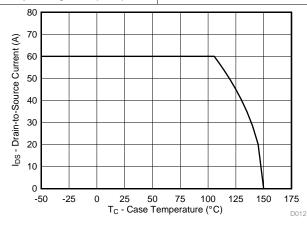


Figure 12. Maximum Drain Current vs Temperature

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Device and Documentation Support

6.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on Alert me to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

6.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community T's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support TI's Design Support Quickly find helpful E2E forums along with design support tools and contact information for technical support.

6.3 Trademarks

NexFET, E2E are trademarks of Texas Instruments. All other trademarks are the property of their respective owners.

Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.5 Glossary

SLYZ022 — TI Glossary.

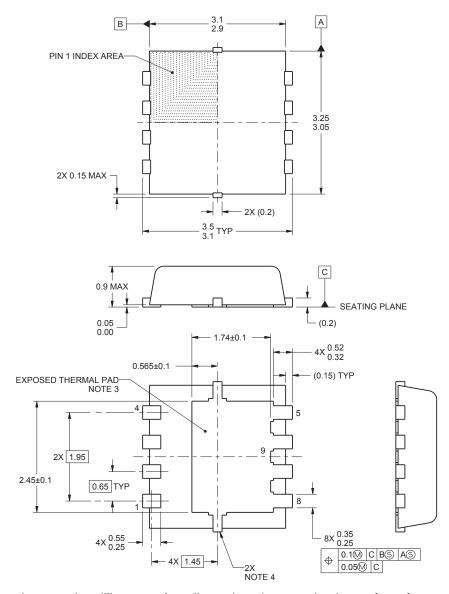
This glossary lists and explains terms, acronyms, and definitions.

TEXAS INSTRUMENTS

7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 Q3A Package Dimensions

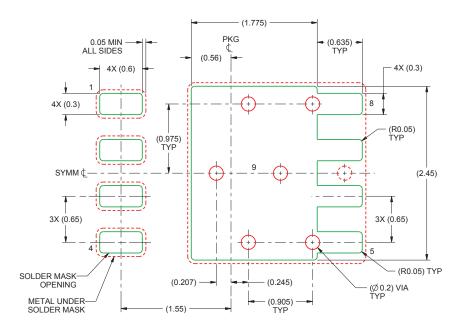


- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.
- 4. Metalized features are supplier options and may not be on the package.
- 5. All dimensions do not include mold flash or protrusions.



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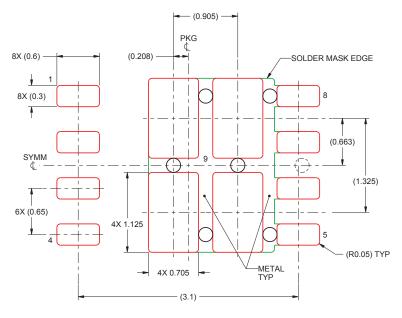
7.2 Q3A Recommended PCB Pattern



- This package is designed to be soldered to a thermal pad on the board. For more information, see QFN/SON PCB Attachment (SLUA271).
- Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.

For recommended circuit layout for PCB designs, see *Reducing Ringing Through PCB Layout Techniques* (SLPA005).

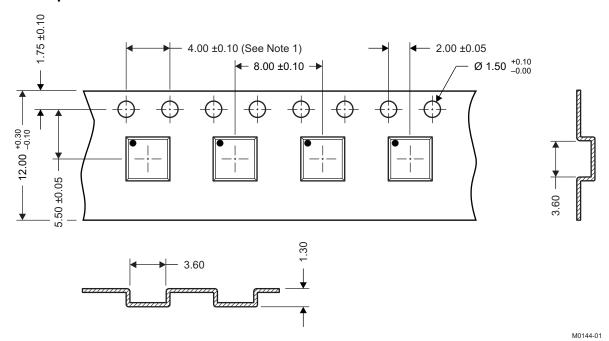
7.3 Q3A Recommended Stencil Pattern



1. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

TEXAS INSTRUMENTS

7.4 Q3A Tape and Reel Information



Notes: 1. 10-sprocket hole-pitch cumulative tolerance ±0.2.

- 2. Camber not to exceed 1 mm in 100 mm, noncumulative over 250 mm.
- 3. Material: black static-dissipative polystyrene.
- 4. All dimensions are in mm, unless otherwise specified.
- 5. Thickness: 0.30 ± 0.05 mm.
- 6. MSL1 260°C (IR and convection) PbF-reflow compatible.

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PACKAGE OPTION ADDENDUM

14-Oct-2016

PACKAGING INFORMATION

Orderable Device	Status	Package Type	_	Pins	_	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
CSD17581Q3A	ACTIVE	VSONP	DNH	8	2500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-55 to 150	17581	Samples
CSD17581Q3AT	ACTIVE	VSONP	DNH	8	250	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-55 to 150	17581	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

14-Oct-2016

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